Unit: mm

TOSHIBA Transistor Silicon PNP Epitaxial Type

TPCP8603

High-Speed Switching Applications DC/DC Converters Strobe Applications

High DC current gain: $h_{FE} = 120 \sim 300 (IC = -0.1 A)$

Low collector-emitter saturation voltage: $V_{CE (sat)} = -0.2 \text{ V (max)}$

High-speed switching: $t_f = 120 \text{ ns (typ.)}$

Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
Collector-vase voltage		V_{CBO}	-120	V
Collector-emitter voltage		V_{CEO}	-120	V
Collector-emitter voltage		V_{EBO}	-7	V
Collector current	DC (Note 1)	Ic	-1.0	Α
	Pulsed (Note 1)	I _{CP}	-2.0	Α
Base current		ΙΒ	0.1	Α
Collector power dissipation	t = 10 s	P _C (Note 2)	3.00	W
	DC	FC (Note 2)	1.25	W
Junction temperature		Tj	150	°C
Storage temperature range		T _{stg}	−55 ~ 150	°C

Note 1: Ensure that the channel temperature does not exceed 150°C during use of the device.

area, 645 mm²)

report and estimated failure rate, etc).

Note 2: Mounted on the FR4 board (glass-epoxy; 1.6 mm thick; Cu Note 3: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook

("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test

♦ 0.05M A 0.475 0.05M B A 0.8±0.05 0.025 S 0.17±0.02 $0.28^{+0.1}_{-0.11}$ $1.12^{+0.13}_{-0.12}$ $1.12^{+0.13}_{-0.12}$ $0.28^{+0.1}_{-0.11}$ 5. Emitter 1. Collector 2. Collector 6. Collector 3. Collector 7. Collector 8. Collector 4. Base JEDEC JEITA

Weight: 0.017 g (typ.)

2-3V1A

TOSHIBA

Figure 1. Circuit Configuration

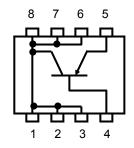
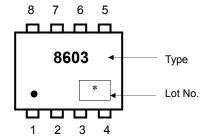
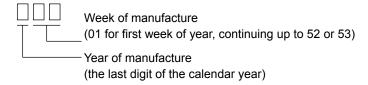


Figure 2. Marking (Note4)



Note 4: • on the lower left of the marking indicates Pin 1.

* Weekly code (three digits):

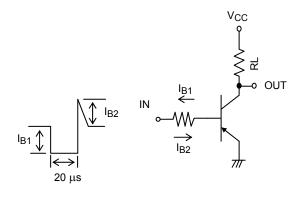


Electrical Characteristics (Ta = 25°C)

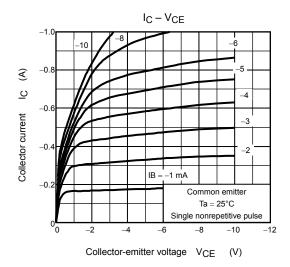
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit	
Collector cutoff current		I _{CBO}	V _{CB} = -120 V, IE = 0	_	_	-100	nA	
Emitter cutoff current		I _{EBO}	$V_{EB} = -7 \text{ V}, I_{C} = 0$	_	_	-100	nA	
Collector-emitter breakdown voltage		V (BR) CEO	$I_C = -10 \text{ mA}, IB = 0$	-120	_	_	V	
DC current gain		hFE(1)	$V_{CE} = -2 \text{ V}, I_{C} = -0.1 \text{ A}$	120	_	300		
		hFE(2)	$V_{CE} = -2 \text{ V}, I_{C} = -0.3 \text{ A}$	60	_	_		
Collector-emitter saturation voltage		V _{CE} (sat)	$I_C = -0.3 \text{ A}, IB = -0.01 \text{ A}$	_	_	-0.2	V	
Base-emitter saturation voltage		V _{BE (sat)}	$I_C = -0.3 \text{ A}, IB = -0.01 \text{ A}$	_	_	-1.1	V	
Switching time	Storage time	t _r	See Figure 3 circuit diagram.	_	130	_		
	Storage time	t _{stg}	$V_{CC} \cong 72 \text{ V}, \text{ RL} = 240 \Omega$	_	650	_	ns	
	Fall time	t _f	−IB1 = IB2 = −10 mA	_	120	_		

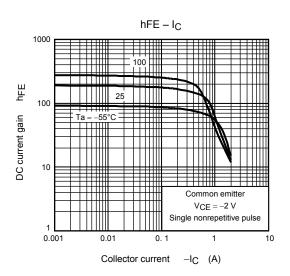
2

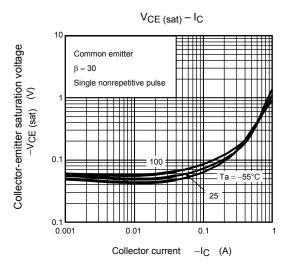
Figure 3. Switching Time Test Circuit & Timing Chart

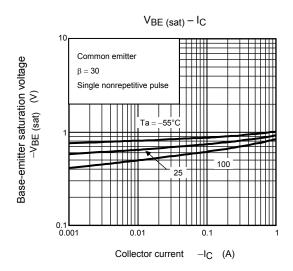


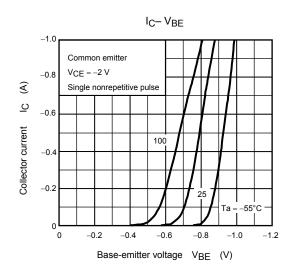
Duty cycle < 1 %





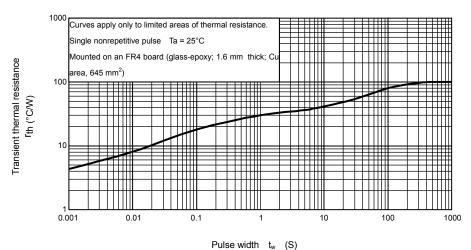




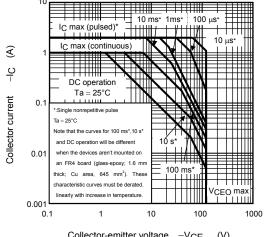


3





Safe Operating Area



Collector-emitter voltage -VCE (V)

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20070701-EN

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